

HAN3A-2**高频高压二极管**

反向电压：2 kV；正向电流：3 A；反向恢复时间：100 ns

High-Speed High Voltage Diode

Reverse Voltage：2 kV

Average Forward Current：3 A

Maximum Reverse Recovery Time：100 ns

技术资料**Technical Data**

- 产品级别：外贸级
- 封装形式：环氧封装
- 引线：轴向
- 极性：色环指示负极
- Product Grade: International Standard
- Package Type: Epoxy Encapsulation
- Lead: Axial lead
- Polarity: Cathode Indicated by Color Band

产品标准**Product Standard**

Q/FT TRV0003-2022 《高压二极管》

验收标准**Acceptance Criteria**

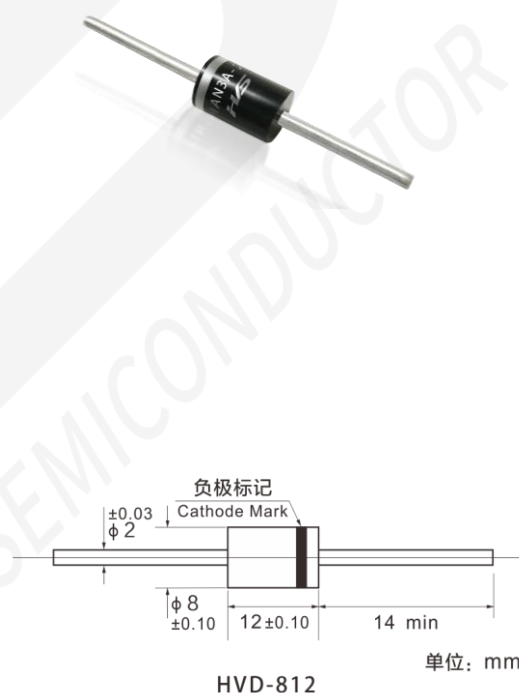
GB/T 4023-1997 《半导体器件分立器件和集成电路 第2部分：整流二极管》

Semiconductor Devices-Discrete Devices and Integrated Circuits-Part 2: Rectifier Diodes

外形尺寸**External Dimensions**

封装代号：HVD-812；详见右图

Package Code: HVD-812; Please refer to the figure on the right.





特性及参数值

Characteristics and Parameter

除非另有规定，环境温度均为 25°C。

The ambient temperature is 25°C unless otherwise specified.

电气特性 Electrical Characteristics	符 号 Symbol	额定值 Ratings	单 位 Unit
最大反向重复峰值电压 Maximum Repetitive Peak Reverse Voltage	V_{RRM}	2	kV
最大反向不重复峰值电压 Maximum Non-repetitive Peak Reverse Voltage	V_{RSM}	2.2	kV
最大正向平均电流 Maximum Average Forward Current (@ $T_{o1} = 55^{\circ}\text{C}$)	$I_{F(AV)}$	3	A
最大正向浪涌电流 Maximum Surge Current	I_{FSM}	80	A
最大正向峰值电压 Maximum Peak Forward Voltage (@ $I_F = I_{F(AV)}$)	V_{FM}	≤ 4	V
最大直流反向电流 Maximum DC Reverse Current (@ $V_R = V_{RRM}$)	I_R	≤ 2 ($T_{o1} = 25^{\circ}\text{C}$)	μA
		≤ 30 ($T_{o1} = 100^{\circ}\text{C}$)	
最大反向恢复时间 Maximum Reverse Recovery Time ($I_F = 0.5\text{A}$, $I_{RM} = 1\text{A}$)	t_{rr}	≤ 100	ns
有效工作结温 Operating Junction Temperature Range	T_J	$-55 \sim +125$	$^{\circ}\text{C}$
贮存温度 Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$